

# Hadis Morko

## List of Publications by Citations

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#	Paper	IF	Citations
173	Luminescence properties of defects in GaN. <i>Journal of Applied Physics</i> , <b>2005</b> , 97, 061301	2.5	1461
172	ZnO Devices and Applications: A Review of Current Status and Future Prospects. <i>Proceedings of the IEEE</i> , <b>2010</b> , 98, 1255-1268	14.3	556
171	Very low resistance multilayer Ohmic contact to n-GaN. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 1672-1674	3.4	390
170	Comprehensive analysis of Si-doped Al <sub>x</sub> Ga <sub>1-x</sub> As (x=0 to 1): Theory and experiments. <i>Physical Review B</i> , <b>1984</b> , 30, 4481-4492	3.3	373
169	Microwave ferrites, part 1: fundamental properties. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2009</b> , 20, 789-834	2.1	280
168	On the efficiency droop in InGaN multiple quantum well blue light emitting diodes and its reduction with p-doped quantum well barriers. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 121107	3.4	275
167	Reduction of efficiency droop in InGaN light emitting diodes by coupled quantum wells. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 171113	3.4	181
166	Doping Asymmetry Problem in ZnO: Current Status and Outlook. <i>Proceedings of the IEEE</i> , <b>2010</b> , 98, 1269-1280	14.3	162
165	GaN-based modulation doped FETs and UV detectors. <i>Solid-State Electronics</i> , <b>2002</b> , 46, 157-202	1.7	137
164	Electron density of the two-dimensional electron gas in modulation doped layers. <i>Journal of Applied Physics</i> , <b>1983</b> , 54, 2093-2096	2.5	111
163	Energy band bowing parameter in Al <sub>x</sub> Ga <sub>1-x</sub> N alloys. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 4837-4839	2.5	108
162	Recombination dynamics of free and localized excitons in GaN/Ga <sub>0.93</sub> Al <sub>0.07</sub> N quantum wells. <i>Physical Review B</i> , <b>1998</b> , 57, R9447-R9450	3.3	103
161	Microwave ferrites, part 2: passive components and electrical tuning. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2009</b> , 20, 911-952	2.1	95
160	Polarization effects in nitride semiconductor device structures and performance of modulation doped field effect transistors. <i>Solid-State Electronics</i> , <b>1999</b> , 43, 1909-1927	1.7	92
159	High electron mobility in nearly lattice-matched AlInN/AlN/GaN heterostructure field effect transistors. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 132116	3.4	91
158	GaN-Based Light-Emitting Diodes: Efficiency at High Injection Levels. <i>Proceedings of the IEEE</i> , <b>2010</b> , 98, 1180-1196	14.3	84
157	Collector-emitter offset voltage in AlGaAs/GaAs heterojunction bipolar transistors. <i>Applied Physics Letters</i> , <b>1985</b> , 47, 313-315	3.4	83

156	Oscillator strengths for optical band-to-band processes in GaN epilayers. <i>Physical Review B</i> , <b>1996</b> , 54, 7678-7681	3.3	76
155	Systematic measurement of Al <sub>x</sub> Ga <sub>1-x</sub> N refractive indices. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 4103-4105	3.4	65
154	Theoretical investigation of electrical characteristics of AlGa <sub>N</sub> /Ga <sub>N</sub> modulation doped field-effect transistors. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 3031-3042	2.5	63
153	High- $\epsilon$ dielectrics and advanced channel concepts for Si MOSFET. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2008</b> , 19, 915-951	2.1	61
152	Dielectric functions and electronic band structure of lead zirconate titanate thin films. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 094108	2.5	59
151	Carrier dynamics in bulk GaN. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 023702	2.5	57
150	GaN epitaxy on thermally treated c-plane bulk ZnO substrates with O and Zn faces. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 2268-2270	3.4	57
149	Recent Development of Boron Nitride towards Electronic Applications. <i>Advanced Electronic Materials</i> , <b>2017</b> , 3, 1600485	6.4	53
148	Photoluminescence characterization of the quantum well structure and influence of optical illumination on the electrical performance of AlGa <sub>N</sub> /Ga <sub>N</sub> modulation-doped field-effect transistors. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 1420-1422	3.4	53
147	High-purity GaAs and Cr-doped GaAs epitaxial layers by MBE. <i>Journal of Applied Physics</i> , <b>1979</b> , 50, 6413-6416	3.6	53
146	Electrical conduction in silicon nitrides deposited by plasma enhanced chemical vapour deposition. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , <b>1996</b> , 73, 723-736		48
145	Suppression of leakage currents and their effect on the electrical performance of AlGa <sub>N</sub> /Ga <sub>N</sub> modulation doped field-effect transistors. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 1229-1231	3.4	45
144	Small Signal Equivalent Circuit Modeling for AlGa <sub>N</sub> /Ga <sub>N</sub> HFET: Hybrid Extraction Method for Determining Circuit Elements of AlGa <sub>N</sub> /Ga <sub>N</sub> HFET. <i>Proceedings of the IEEE</i> , <b>2010</b> , 98, 1140-1150	14.3	44
143	Photoreflectance investigations of the bowing parameter in AlGa <sub>N</sub> alloys lattice-matched to Ga <sub>N</sub> . <i>Applied Physics Letters</i> , <b>1999</b> , 74, 3353-3355	3.4	43
142	Surface band bending in as-grown and plasma-treated n-type Ga <sub>N</sub> films using surface potential electric force microscopy. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 3070-3072	3.4	39
141	Transport properties of Sn-doped Al <sub>x</sub> Ga <sub>1-x</sub> As grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>1980</b> , 51, 4882-4884	2.5	39
140	InGa <sub>N</sub> light-emitting diodes: Efficiency-limiting processes at high injection. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2013</b> , 31, 050809	2.9	37
139	Fabrication and current-voltage characterization of a ferroelectric lead zirconate titanate/AlGa <sub>N</sub> /Ga <sub>N</sub> field effect transistor. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 123508	3.4	36

138	Bulk ZnO: Current Status, Challenges, and Prospects. <i>Proceedings of the IEEE</i> , <b>2010</b> , 98, 1339-1350	14.3	35
137	Metal-insulator-semiconductor structures on p-type GaAs with low interface state density. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 230-232	3.4	35
136	In situ transmission electron microscopy of AlN growth by nitridation of (0001) $\beta$ -Al <sub>2</sub> O <sub>3</sub> . <i>Journal of Applied Physics</i> , <b>1998</b> , 83, 2847-2850	2.5	34
135	Cathodoluminescence measurement of an orientation dependent aluminum concentration in Al <sub>x</sub> Ga <sub>1-x</sub> As epilayers grown by molecular beam epitaxy on a nonplanar substrate. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 1347-1349	3.4	31
134	III-Nitride semiconductor growth by MBE: Recent issues. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2001</b> , 12, 677-695	2.1	29
133	Status of Growth of Group III-Nitride Heterostructures for Deep Ultraviolet Light-Emitting Diodes. <i>Crystals</i> , <b>2017</b> , 7, 300	2.3	28
132	Status of Reliability of GaN-Based Heterojunction Field Effect Transistors. <i>Proceedings of the IEEE</i> , <b>2010</b> , 98, 1127-1139	14.3	28
131	Structural and electrical properties of Pb(Zr,Ti)O <sub>3</sub> grown on (0001) GaN using a double PbTiO <sub>3</sub> /BbO bridge layer. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 182908	3.4	27
130	Purity of GaAs grown by LPE in a graphite boat. <i>Journal of Crystal Growth</i> , <b>1976</b> , 36, 109-114	1.6	27
129	Ti/Al/Ni/Au Ohmic contacts for AlInN/AlN/GaN-based heterojunction field-effect transistors. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 014508	2.5	26
128	Properties of GaAs on Si grown by molecular beam epitaxy. <i>Critical Reviews in Solid State and Materials Sciences</i> , <b>1990</b> , 16, 91-114	10.1	26
127	Experimental study of the frequency limits of a resonant tunneling oscillator. <i>Applied Physics Letters</i> , <b>1986</b> , 48, 422-424	3.4	25
126	Large pyroelectric effect in undoped epitaxial Pb(Zr,Ti)O <sub>3</sub> thin films on SrTiO <sub>3</sub> substrates. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 052913	3.4	24
125	Resonant surface plasmon-induced modification of photoluminescence from GaN/AlN quantum dots. <i>Nanotechnology</i> , <b>2004</b> , 15, 1252-1255	3.4	24
124	Ferromagnetism in ZnO- and GaN-Based Diluted Magnetic Semiconductors: Achievements and Challenges. <i>Proceedings of the IEEE</i> , <b>2010</b> , 98, 1288-1301	14.3	23
123	Temperature dependence of current gain in AlGaAs/GaAs heterojunction bipolar transistors. <i>Applied Physics Letters</i> , <b>1984</b> , 45, 1086-1088	3.4	23
122	An alternative material for transparent antennas for commercial and medical applications. <i>Microwave and Optical Technology Letters</i> , <b>2017</b> , 59, 773-777	1.2	22
121	Defect reduction in GaN epilayers grown by metal-organic chemical vapor deposition with in situ SiN <sub>x</sub> nanonetwork. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 262112	3.4	20

120	Chromium and tellurium redistribution in GaAs and Al <sub>0.3</sub> Ga <sub>0.7</sub> As grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>1980</b> , 51, 5986-5991	2.5	20
119	Low-Frequency Noise Measurements of AlGaN/GaN MetalOxideSemiconductor Heterostructure Field-Effect Transistors With HfAlO Gate Dielectric. <i>IEEE Electron Device Letters</i> , <b>2010</b> , 31, 1041-1043	4.4	19
118	High quality epitaxial growth of PbTiO <sub>3</sub> by molecular beam epitaxy using H <sub>2</sub> O <sub>2</sub> as the oxygen source. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 122912	3.4	18
117	GROWTH, STRUCTURES, AND OPTICAL PROPERTIES OF III-NITRIDE QUANTUM DOTS. <i>International Journal of High Speed Electronics and Systems</i> , <b>2002</b> , 12, 79-110	0.5	18
116	Epitaxial growth of (001)-oriented Ba <sub>0.5</sub> Sr <sub>0.5</sub> TiO <sub>3</sub> thin films on a-plane sapphire with an MgO/ZnO bridge layer. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 212901	3.4	17
115	Effect of carrier spillover and Auger recombination on the efficiency droop in InGaN-based blue LEDs. <i>Superlattices and Microstructures</i> , <b>2010</b> , 47, 118-122	2.8	16
114	Large electro-optic effect in single-crystal Pb(Zr,Ti)O <sub>3</sub> (001) measured by spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 093103	2.5	16
113	Polarization effects in nitride semiconductors and device structures. <i>Materials Research Innovations</i> , <b>1999</b> , 3, 97-106	1.9	16
112	Effect of large strain on dielectric and ferroelectric properties of Ba <sub>0.5</sub> Sr <sub>0.5</sub> TiO <sub>3</sub> thin films. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 012907	3.4	15
111	Field-assisted emission in AlGaN/GaN heterostructure field-effect transistors using low-frequency noise technique. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 084522	2.5	15
110	Visible-ultraviolet spectroscopic ellipsometry of lead zirconate titanate thin films. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 262902	3.4	15
109	Polarity control and residual strain in ZnO epilayers grown by molecular beam epitaxy on (0001) GaN/sapphire. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2016</b> , 10, 682-686	2.5	14
108	General Properties of ZnO <b>2009</b> , 1-76		14
107	I-V characteristics of AuNi Schottky diodes on GaN with SiN <sub>x</sub> nanonetwork. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 152108	3.4	14
106	Infrared optical absorbance of intersubband transitions in GaN/AlGaN multiple quantum well structures. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 10140-10142	2.5	14
105	A pnp AlGaAs/GaAs heterojunction bipolar transistor. <i>Applied Physics Letters</i> , <b>1985</b> , 46, 302-304	3.4	13
104	Enhanced microwave dielectric tunability of Ba <sub>0.5</sub> Sr <sub>0.5</sub> TiO <sub>3</sub> thin films grown with reduced strain on DyScO <sub>3</sub> substrates by three-step technique. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 044108	2.5	12
103	Minority-carrier characteristics of SiN <sub>x</sub> /GaAs metalInsulatorSemiconductor structures with Si/Ge interlayers. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 1210-1212	3.4	12

102	Proposed explanation of the anomalous doping characteristics of III-V nitrides. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , <b>1997</b> , 76, 131-143		12
101	Near-infrared wavelength intersubband transitions in GaN/AlN short period superlattices. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 1511-12	3.4	12
100	Interface properties of Si <sub>3</sub> N <sub>4</sub> /Si/n-GaAs metal-insulator-semiconductor structure using a Si interlayer. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , <b>1996</b> , 74, 219-234		12
99	Saga of efficiency degradation at high injection in InGaN light emitting diodes. <i>Turkish Journal of Physics</i> , <b>2014</b> , 38, 269-313	1.6	11
98	Stimulated emission and ultrafast carrier relaxation in AlGaN/GaN multiple quantum wells. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 4080-4082	3.4	11
97	Improvement of optical quality of semipolar (112̄) GaN on m-plane sapphire by in-situ epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 145303	2.5	10
96	Thickness variations and absence of lateral compositional fluctuations in aberration-corrected STEM images of InGaN LED active regions at low dose. <i>Microscopy and Microanalysis</i> , <b>2014</b> , 20, 864-8	0.5	9
95	The Growth of Uniform Submicron GaAs Layers by Liquid Phase Epitaxy. <i>Journal of the Electrochemical Society</i> , <b>1976</b> , 123, 906-912	3.9	9
94	Hot phonons in InAlN/AlN/GaN heterostructure 2DEG channels <b>2009</b> ,		8
93	Generation-Recombination noise in gallium nitride-based quantum well structures. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 5337-5345	2.5	8
92	Characteristics of Si <sub>3</sub> N <sub>4</sub> /Si/n-GaAs metal-insulator-semiconductor interfaces grown on GaAs(111)B substrate. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 3025-3027	3.4	8
91	Group III Nitrides. <i>Springer Handbooks</i> , <b>2017</b> , 1-1	1.3	7
90	Characterization of Ag Schottky Barriers on Be <sub>0.02</sub> Mg <sub>0.26</sub> ZnO/ZnO Heterostructures. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2018</b> , 12, 1700366	2.5	7
89	Zinc Oxide Materials and Devices Grown by Molecular Beam Epitaxy <b>2018</b> , 343-375		7
88	Photoluminescence of Mg-doped m-plane GaN grown by MOCVD on bulk GaN substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2011</b> , 208, 1532-1534	1.6	6
87	Si <sub>3</sub> N <sub>4</sub> /Si/In <sub>0.05</sub> Ga <sub>0.95</sub> As/n-GaAs metal-insulator-semiconductor devices. <i>Journal of Applied Physics</i> , <b>1997</b> , 81, 516-523	2.5	6
86	POLARIZATION EFFECTS IN NITRIDE SEMICONDUCTOR HETEROSTRUCTURES. <i>International Journal of High Speed Electronics and Systems</i> , <b>2000</b> , 10, 25-37	0.5	6
85	Indium-incorporation efficiency in semipolar (11-22) oriented InGaN-based light emitting diodes <b>2015</b> ,		5

84	Measurement of the minority-carrier lifetime and injection efficiency in AlGaAs/GaAs heterojunction bipolar transistors. <i>Applied Physics Letters</i> , <b>1986</b> , 48, 367-369	3-4	5
83	Modulation Doped Al <sub>x</sub> Ga <sub>1-x</sub> As/GaAs Field Effect Transistors (MODFETS): Analysis, Fabrication and Performance <b>1985</b> , 625-676		5
82	Doping of ZnO <b>2009</b> , 245-275		4
81	Microstructure and field mapping of AlInN-based heterostructures and devices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2010</b> , 7, 2436-2439		4
80	Metal/Insulator/Semiconductor structure on GaAs using a pseudomorphic Si/GaP interlayer. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1997</b> , 15, 252		4
79	Structural and Optical Properties of PbTiO <sub>3</sub> Grown on SrTiO <sub>3</sub> Substrates by Peroxide MBE. <i>Materials Research Society Symposia Proceedings</i> , <b>2006</b> , 966, 1		4
78	Megahertz bandwidth Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN-based p-i-n detectors <b>1998</b> , 3287, 198		4
77	A Platform for Complementary Metal-Oxide-Semiconductor Compatible Plasmonics: High Plasmonic Quality Titanium Nitride Thin Films on Si (001) with a MgO Interlayer. <i>Advanced Photonics Research</i> , <b>2021</b> , 2, 2000210	1.9	4
76	Active region dimensionality and quantum efficiencies of InGaN LEDs from temperature dependent photoluminescence transients <b>2015</b> ,		3
75	Measurements of generation-recombination effect by low-frequency phase-noise technique in AlGaIn/GaN MOSHFETs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 1539-1543		3
74	Optical Properties <b>2009</b> , 131-244		3
73	Reduction of Flicker Noise in AlGaIn/GaN-Based HFETs After High Electric-Field Stress. <i>IEEE Electron Device Letters</i> , <b>2011</b> , 32, 1513-1515	4-4	3
72	Studies of III-Nitride Superlattice Structures Implanted with Lanthanide Ions. <i>Materials Research Society Symposia Proceedings</i> , <b>2008</b> , 1111, 1		3
71	Epitaxial growth of ZrO <sub>2</sub> on GaN templates by oxide molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 022916	3-4	3
70	Polarity Control within One Monolayer at ZnO/GaN Heterointerface: (0001) Plane Inversion Domain Boundary. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 37651-37660	9-5	3
69	Group III Nitrides <b>2006</b> , 753-804		3
68	Enhancement of optical and structural quality of semipolar (11-22) GaN by introducing nanoporous SiN <sub>x</sub> interlayers <b>2015</b> ,		2
67	Strong carrier localization in stacking faults in semipolar (11-22) GaN <b>2015</b> ,		2



66	Carrier dynamics under two- and single-photon excitation in bulk GaN. <i>Physica Status Solidi (B): Basic Research</i> , <b>2012</b> , 249, 503-506	1.3	2
65	Light-Emitting Diodes and Lighting <b>2013</b> , 209-266		2
64	ZnO Nanostructures <b>2009</b> , 365-386		2
63	Bandgap Engineering <b>2009</b> , 351-364		2
62	Intrinsic Polarization of Self-Assembled Guanosine Supramolecules in GaN-Based Metal-Semiconductor-Metal Nano-Structures. <i>Journal of Display Technology</i> , <b>2009</b> , 5, 446-451		2
61	Stress test measurements of lattice-matched InAlN/AlN/GaN HFET structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2010</b> , 207, 1345-1347	1.6	2
60	On the inversion in GaAs metal-insulator-semiconductor heterostructures. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 228-230	3.4	2
59	Characteristics of Si <sub>3</sub> N <sub>4</sub> /GaAs metal-insulator-semiconductor interfaces with coherent Si/Al <sub>0.3</sub> Ga <sub>0.7</sub> As interlayers. <i>Journal of Electronic Materials</i> , <b>1997</b> , 26, 1076-1082	1.9	2
58	Polarization in GaN Based Heterostructures and Heterojunction Field Effect Transistors (HFETs) <b>2008</b> , 373-466		2
57	Field Effect Transistors and Heterojunction Bipolar Transistors 349-707		2
56	Growth of High-Quality Pb(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> Films by Peroxide MBE and Their Optical and Structural Characteristics. <i>Materials Research Society Symposia Proceedings</i> , <b>2006</b> , 966, 1		2
55	Effects of Rapid Thermal Annealing Treatment on the Surface Band Bending of n-type GaN Studied by Surface Potential Electric Force Microscopy. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 1529-1532	0.4	2
54	Influence of ZnO thin film crystallinity on biocompatibility. <i>Toxicology Research</i> , <b>2018</b> , 7, 754-759	2.6	2
53	Modulation-Doped Field-Effect Transistors (MODFET) <b>2015</b> , 1-50		1
52	The effect of barrier strain on the reliability of In <sub>x</sub> Al <sub>1-x</sub> N/AlN/GaN heterostructure field-effect transistors. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2012</b> , 6, 163-165	2.5	1
51	Carrier Transport <b>2013</b> , 115-175		1
50	General Properties of Nitrides <b>2013</b> , 1-61		1
49	Growth and Characterization of GaN/ZnO Heteroepitaxy and ZnO-Based Hybrid Devices <b>2011</b> , 221-264		1



48	On the Light Emission in GaN Based Heterostructures at High Injection. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1202, 23		1
47	Investigation of Epitaxially Grown PbO, TiO <sub>2</sub> and ZrO <sub>2</sub> as Bridge Layers for Integration of PZT on GaN by MBE. <i>Materials Research Society Symposia Proceedings</i> , <b>2006</b> , 966, 1		1
46	GaN-Based Modulation-Doped FETs and Heterojunction Bipolar Transistors <b>2006</b> , 547-626		1
45	Electronic Band Structure of Bulk and QW Nitrides. <i>Springer Series in Materials Science</i> , <b>1999</b> , 45-82	0.9	1
44	High-Performance BeMgZnO/ZnO Heterostructure Field-Effect Transistors. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2020</b> , 14, 2000371	2.5	1
43	High-Quality Plasmonic Materials TiN and ZnO:Al by Atomic Layer Deposition. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2021</b> , 15, 2100227	2.5	1
42	New high-speed (Al, Ga) as modulation doped field-effect transistors. <i>IEEE Circuits and Devices: the Magazine of Electronic and Photonic Systems</i> , <b>1985</b> , 1, 35-38		0
41	III-Nitride Light-Emitting Diodes <b>2017</b> , 1-21		
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39	Semiconductor Lasers: Light Amplification by Stimulated Emission of Radiation <b>2013</b> , 267-348		
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